Inventor: Winston G. Scott

Title: Methods of Forming Transistor Gates; and Methods of Forming Programmable Read-Only Memory Constructions

Assignee: Micron Technology, Inc.

EV317136345

INFORMATION DISCLOSURE STATEMENT

PURSUANT TO 37 C.F.R. §§1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation of co-pending application Serial No. 09/876,722 filed June 6, 2001. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. §1.98(d) and MPEP §609(2). No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: 8/5/2003 Attorney: _____

David G. Latwesen, Ph.D.
Reg. #38,533
WELLS ST. JOHN P.S.

EV317136345

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-2375	PRIORITY SERIAL NO. 09/876,722
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT Winston G. Scott	
		PRIORITY FILING DATE 6/6/01	PRIORITY GROUP 2812

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	6,033,952	03/00	Yasumura et al.			
	AB	6,124,168	9/2000	Ong			
	AC	5,668,705	11/97	Bergemont			
	AD	5,866,448	2/99	Pradeep et al.			
	AE	5,858,847	1/99	Zhou et al.			
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AM							
	AN							
	AO							
	AP							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AR		Watanabe, H. et al., "Novel 0.44μm^2 Ti-Salicide STI Cell Technology for High-Density NOR Flash Memories and High Performance
			Embedded Application", IEEE 1998, pp. 36.2.1 - 36.2.4.
	AS		Wolf, S., "Silicon Processing for the VLSI Era", Vol. 2, pp. 632-635.
	AT		MITSUBISHI ELECTRIC WEBSITE: Reprinted from website http://www.mitsubishielectric.com/r and d/tech showcase/ts8.php on
			3/29/2001: "8. Production Line Application of a Fine Hole Pattern-Formation Technology for Semiconductors", on 3/29/2001, 4 pgs.

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

EV317136345

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-2375	PRIORITY SERIAL NO. 09/876,722
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT Winston G. Scott	
		PRIORITY FILING DATE 6/6/01	PRIORITY GROUP 2812

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AM							
	AN							
	AO							
	AP							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AR		CAHNERS SEMICONDUCTOR INTERNATIONAL WEBSITE: Reprinted from http://www.semiconductor.net/semiconductor/issues/
			1999/sep99/docs/feature1.asp on 3/29/2001: "Resists Join the Sub-λ Revolution", 9 pgs.
	AS		CAHNERS SEMICONDUCTOR INTERNATIONAL WEBSITE: Reprinted from http://www.semiconductor.net/semiconductor/issues/
			1999/aug99/docs/lithography.asp on 3/29/2001: "Paths to Smaller Features", 1 pg.
	AT		

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.